REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Add device type 02. Add vendor CAGE 27014. Add case outlines C and D. Technical and editorial changes throughout.	91-12-30	M. A. Frye
B	Changes in accordance with 5962-R135-92	92-07-31	Thomas M. Hess
C	Add vendor CAGE 01295 for device type 02. Change drawing format to incorporate device class V criteria. - jak	97-09-05	Monica L. Poelking
D	Add Radiation Hardened Assurance limits. - jak	98-05-29	Monica L. Poelking
E	Add Vendor CAGE code F8859. Correct title to accurately describe device function. Add device type 03. Add case outline X. Add radiation features to device type 02. Update boilerplate to MIL-PRF-38535 requirements. – LTG	02-07-19	Thomas M. Hess
F	Add radiation features for device type 03 in section 1.5. Make changes to $V_{IC}+$, $V_{IC}-$, I_{CCH}, and I_{CCL} limits for device type 03 in table I. Update the boilerplate to include radiation hardness assured requirements for device type 03. Editorial changes throughout. - jak	04-08-18	Thomas M. Hess

REV																				
SHEET																				
REV	F	F																		
SHEET	15	16																		

REV STATUS OF SHEETS	REV	F	F	F	F	F	F	F	F	F	F	F	F	F	F
	SHEET	1	2	3	4	5	6	7	8	9	10	11	12	13	14

PMIC N/A

PREPARED BY
Marcia B. Kelleher

DEFENSE SUPPLY CENTER COLUMBUS

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STANDARD MICROCIRCUIT DRAWING

THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE

AMSC N/A

CHECKED BY
Thomas J. Ricciuti

APPROVED BY
Michael A. Frye

DRAWING APPROVAL DATE
89-04-10

REVISION LEVEL
F

MICROCIRCUIT, DIGITAL, ADVANCED CMOS, QUAD TWO-INPUT AND GATE, TTL COMPATIBLE INPUTS, MONOLITHIC SILICON

SIZE	CAGE CODE	
A	**67268**	**5962-89547**

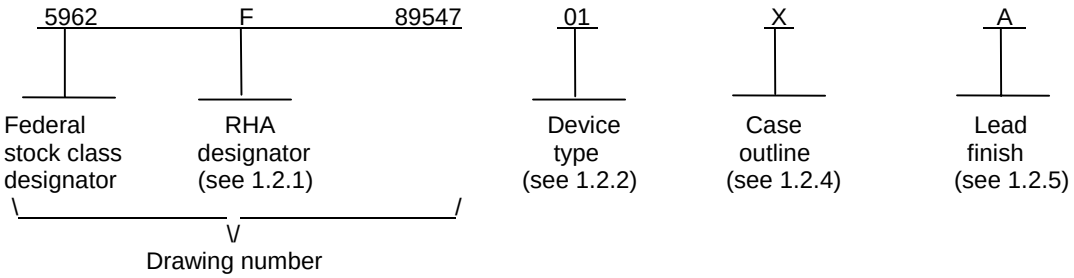
SHEET
1 OF 16

1. SCOPE

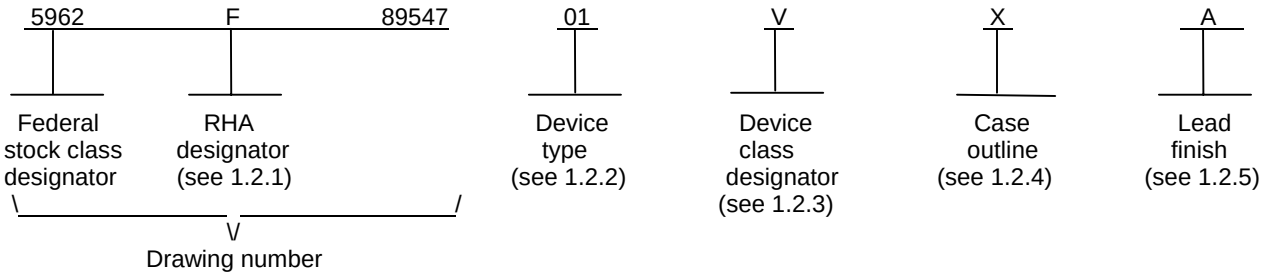
1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:

For device classes M and Q:



For device class V:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function
01	54ACT11008	Quad two-input AND gate, TTL compatible inputs
02	54ACT08	Quad two-input AND gate, TTL compatible inputs
03	54ACT08	Quad two-input AND gate, TTL compatible inputs

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as listed below. Since the device class designator has been added after the original issuance of this drawing, device classes M and Q designators will not be included in the PIN and will not be marked on the device.

Device class	Device requirements documentation
M	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
C	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14 or CDFP2-F14	14	Flat pack
E	GDIP1-T16 or CDIP2-T16	16	Dual-in-line
X	CDFP3-F14	14	Flat pack
2	CQCC1-N20	20	Square leadless chip carrier

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

1.3 Absolute maximum ratings. 1/ 2/ 3/

Supply voltage range (V_{CC}) ..... -0.5 V dc to +7.0 V dc
DC input voltage range (V_{IN}) ..... -0.5 V dc to V_{CC} + 0.5 V dc
DC output voltage range (V_{OUT}) ..... -0.5 V dc to V_{CC} + 0.5 V dc
DC input diode current (I_{IK}) ..... ±20 mA
DC output diode current (I_{OK}) ..... ±50 mA
DC output current (I_{OUT}) ..... ±50 mA
DC V_{CC} or GND current (I_{CC}, I_{GND}) ..... ±100 mA 4/
Maximum power dissipation (P_D) ..... 440 mW
Storage temperature range (T_{STG}) ..... -65°C to +150°C
Lead temperature (soldering, 10 seconds):
Case outline X ..... +260°C
All other case outlines except case X ..... +300°C
Thermal resistance, junction-to-case (θ_{JC}) ..... See MIL-STD-1835
Junction temperature (T_J) ..... +175°C

1.4 Recommended operating conditions. 2/ 3/ 5/

Supply voltage range (V_{CC}) ..... 4.5 V dc to +5.5 V dc
Minimum high level input voltage (V_{IH}) ..... 2.0 V dc
Maximum low level input voltage (V_{IL}) ..... 0.8 V dc
Input voltage range (V_{IN}) ..... +0.0 V dc to V_{CC}
Output voltage range (V_{OUT}) ..... +0.0 V dc to V_{CC}
Maximum input rise or fall rate ($\Delta t/\Delta v$) ..... 0 to 8 ns/V
Case operating temperature range (T_C) ..... -55°C to +125°C

1.5 Radiation features.

Device type 02:
Maximum total dose available (dose rate = 50 – 300 rads (Si)/s) ..... 100 krads (Si)
Single Event Latch-up (SEL) ..... ≥ 100 MeV-cm^2/mg
Device type 03:
Maximum total dose available (dose rate = 50 – 300 rads (Si)/s) ..... 300 krads (Si)
Single Event Latchup (SEL) ..... ≥ 93 MeV-cm^2/mg

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
2/ Unless otherwise noted, all voltages are referenced to GND.
3/ The limits for the parameters specified herein shall apply over the full specified V_{CC} range and case temperature range of -55°C to +125°C.
4/ For packages with multiple V_{CC} and GND pins, this value represents the total current into all V_{CC} or GND pins.
5/ Unused inputs must be held high or low to prevent them from floating.

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.
MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at http://assist.daps.dla.mil/quicksearch/ or www.dodssp.daps.mil or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 Non-Government publications. The following document(s) form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

ELECTRONIC INDUSTRIES ALLIANCE (EIA)

EIA/JEDEC Standard No. 78 - IC Latch-Up Test

JEDEC Standard No. 20 - Standard for Description of 54/74ACXXXX and 54/74ACTXXXX Advanced High-Speed CMOS Devices

(Copies of these documents are available online at http://www.jedec.org or from the Electronic Industries Alliance, 2500 Wilson Boulevard, Arlington, VA 22201-3834.)

2.3 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Truth table. The truth table shall be as specified on figure 2.

3.2.4 Logic diagram. The logic diagram shall be as specified on figure 3.

3.2.5 Switching waveforms and test circuit. The switching waveforms and test circuit shall be as specified on figure 4.

3.2.6 Radiation exposure circuit. The radiation exposure circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 Notification of change for device class M. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change that affects this drawing.

3.9 Verification and review for device class M. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 36 (see MIL-PRF-38535, appendix A).

TABLE I. Electrical performance characteristics.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ 3/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified		Device type and 4/ device class	V_{CC}	Group A subgroups	Limits 5/		Unit
							Min	Max	
Positive input clamp voltage 3022	V_{IC+} 6/ 7/	For input under test, I_{IN} = 18 mA		01, 02	4.5 V	1, 2, 3		5.7	V
			M, D, P, L, R	02	4.5 V	1		5.7	
		For input under test, I_{IN} = 1 mA		03	Open	1, 2, 3	0.4	1.5	
Negative input clamp voltage 3022	V_{IC-} 6/ 7/	For input under test, I_{IN} = -18 mA		01, 02	4.5 V	1, 2, 3		-1.2	V
			M, D, P, L, R	02	4.5 V	1		-1.2	
		For input under test, I_{IN} = -1 mA		03	0.0 V	1, 2, 3	-0.4	-1.5	
High level output voltage 3006	V_{OH} 6/ 7/ 8/	V_{IN} = 2.0 V or 0.8 V I_{OH} = -50 µA		All	4.5 V	1, 2, 3	4.4		V
				All	5.5 V	1, 2, 3	5.4		
			M, D, P, L, R	02	5.5 V	1	5.4		
		V_{IN} = 2.0 V or 0.8 V I_{OH} = -24 mA		All	4.5 V	1, 2, 3	3.7		
			M, D, P, L, R	02	4.5 V	1	3.7		
				All	5.5 V	1, 2, 3	4.7		
		V_{IN} = 2.0 V or 0.8 V I_{OH} = -50 mA		All	5.5 V	1, 2, 3	3.85		
			M, D, P, L, R	02	5.5 V	1	3.85		
Low level output voltage 3007	V_{OL} 6/ 7/ 8/	V_{IN} = 2.0 V or 0.8 V I_{OL} = 50 µA		All	4.5 V	1, 2, 3		0.1	V
				All	5.5 V	1, 2, 3		0.1	
			M, D, P, L, R	02	5.5 V	1		0.1	
		V_{IN} = 2.0 V or 0.8 V I_{OL} = 24 mA		All	4.5 V	1, 2, 3		0.5	
			M, D, P, L, R	02	4.5 V	1		0.5	
				All	5.5 V	1, 2, 3		0.5	
		V_{IN} = 2.0 V or 0.8 V I_{OL} = 50 mA		All	5.5 V	1, 2, 3		1.65	
			M, D, P, L, R	02	5.5 V	1		1.65	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ 3/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified		Device type and 4/ device class	V_{CC}	Group A subgroups	Limits 5/ Min	Limits 5/ Max	Unit
Input leakage current high 3010	I_{IH} 6/ 7/	V_{IN} = 5.5 V		All All	5.5 V	1, 2, 3		1.0	µA
			M, D, P, L, R	02 All	5.5 V	1		0.1	
Input leakage current low 3009	I_{IL} 6/ 7/	V_{IN} = 0.0 V		All All	5.5 V	1, 2, 3		-1.0	µA
			M, D, P, L, R	02 All	5.5 V	1		-0.1	
Quiescent supply current delta, TTL input levels 3005	ΔI_{CC} 6/ 7/	V_{IL} = 0.0 V, V_{IH} = V_{CC} - 2.1 V All other inputs, V_{IN} = 0.0 V or V_{CC}		All All	5.5 V	1, 2, 3		1.6	mA
			M, D	02		1		1.6	
	9/		P, L, R	All				3.5	
Quiescent supply current high 3005	I_{CCH} 6/ 7/	V_{IN} = V_{CC} or GND I_{OUT} = 0.0 mA		01, 02 All	5.5 V	1, 2, 3		40	µA
				03		1		2	
				All		2, 3		40	
			M	02		1		100	
			D	All				1.0	mA
			P, L, R					3.5	
			M, D, P, L, R, F 10/	03 Q, V				50.0	µA
Quiescent supply current low 3005	I_{CCL} 6/ 7/	V_{IN} = V_{CC} or GND I_{OUT} = 0.0 mA		01, 02 All	5.5 V	1, 2, 3		40	µA
				03		1		2	
				All		2, 3		40	
			M	02		1		100	
			D	All				1.0	mA
			P, L, R					3.5	
			M, D, P, L, R, F 10/	03 Q, V				50.0	µA
Input capacitance 3012	C_{IN}	See 4.4.1c		All All	0.0 V	4		8.0	pF
Power dissipation capacitance	C_{PD} 11/	See 4.4.1c		01 All	5.0 V	4		60	pF
				02, 03 All				72	
Latch-up input/output over-voltage	I_{CC} (O/V1) 12/	$t_w \ge 100$ µs, $t_{cool} \ge t_w$ 5 µs ≤ t_r ≤ 5 ms 5 µs ≤ t_f ≤ 5 ms V_{test} = 6.0 V, V_{CCQ} = 5.5 V V_{over} = 10.5 V See 4.4.1d		All V	5.5 V	2		200	mA
Latch-up input/output positive over-current	I_{CC} (O/I1+) 12/	$t_w \ge 100$ µs, $t_{cool} \ge t_w$ 5 µs ≤ t_r ≤ 5 ms 5 µs ≤ t_f ≤ 5 ms V_{test} = 6.0 V, V_{CCQ} = 5.5 V $I_{trigger}$ = +120 mA See 4.4.1d		All V	5.5 V	2		200	mA

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ 3/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified		Device type and 4/ device class	V_{CC}	Group A subgroups	Limits 5/		Unit
							Min	Max	
Latch-up input/output negative over-current	I_{CC} (O/I1-) 12/	$t_w \ge 100\ \mu s$, $t_{cool} \ge t_w$ $5\ \mu s \le t_r \le 5\ ms$ $5\ \mu s \le t_f \le 5\ ms$ $V_{test} = 6.0\ V$, $V_{CCQ} = 5.5\ V$ $I_{trigger} = -120\ mA$ See 4.4.1d		All V	5.5 V	2		200	mA
Latch-up supply over-voltage	I_{CC} (O/V2) 12/	$t_w \ge 100\ \mu s$, $t_{cool} \ge t_w$ $5\ \mu s \le t_r \le 5\ ms$ $5\ \mu s \le t_f \le 5\ ms$ $V_{test} = 6.0\ V$, $V_{CCQ} = 5.5\ V$ $V_{over} = 9.0\ V$ See 4.4.1d		All V	5.5 V	2		100	mA
Functional tests 3014	6/ 7/ 13/	See 4.4.1b Verify output V_{OUT}		All All	4.5 V	7, 8	L	H	
					5.5 V		L	H	
			M, D, P, L, R	02 All	4.5 V	7	L	H	
Propagation delay time, mA, mB to mY 3003	t_{PLH} 6/ 7/ 14/	$C_L = 50\ pF$ $R_L = 500\Omega$ See figure 4		01 All	4.5 V	9	1.0	8.0	ns
				02 All			1.0	7.0	
				03 All			1.0	8.0	
			M, D, P, L, R	02 All		9	1.0	7.0	
				01 All		10, 11	1.0	9.4	
				02 All			1.0	7.5	
				03 All			1.0	9.0	
	t_{PHL} 6/ 7/ 14/			01 All	4.5 V	9	1.0	7.7	
				02 All			1.0	7.0	
				03 All			1.0	8.0	
			M, D, P, L, R	02 All		9	1.0	7.0	
				01 All		10, 11	1.0	8.6	
				02 All			1.0	7.5	
				03 All			1.0	9.0	

See footnotes on next sheet.

TABLE I. Electrical performance characteristics - Continued.

1/ For tests not listed in the referenced MIL-STD-883, (e.g. ΔICC), utilize the general test procedure under the conditions listed herein. All inputs and outputs shall be tested, as applicable, to the tests in table I herein.

2/ Each input/output, as applicable, shall be tested at the specified temperature, for the specified limits, to the tests in table I herein. Output terminals not designated shall be high level logic, low level logic, or open, except for the I_{CC} and ΔI_{CC} tests, the output terminal shall be open. When performing the I_{CC} and ΔI_{CC} tests, the current meter shall be placed in the circuit such that all current flows through the meter.

3/ RHA parts for device type 02 are tested at all levels M, D, P, L, and R of irradiation. Pre and post irradiation values are identical unless otherwise specified in table I.

RHA parts for device type 03 meet all levels M, D, P, L, R, and F of irradiation. However, these parts are only tested at the "F" level. Pre and post irradiation values are identical unless otherwise specified in table I.

When performing post irradiation electrical measurements for any RHA level for any device, T_A = +25 °C.

4/ The word "All" in the device type and device class column, means limits for all device types and classes.

5/ For negative and positive voltage and current values, the sign designates the potential difference in reference to GND and the direction of current flow, respectively; and the absolute value of the magnitude, not the sign, is relative to the minimum and maximum limits, as applicable, listed herein.

6/ RHA samples do not have to be tested at -55°C and +125°C postirradiation.

7/ When performing postirradiation electrical measurements for RHA level, T_A = +25°C. Limits shown are guaranteed at T_A = +25°C ±5°C.

8/ The V_{OH} and V_{OL} tests shall be tested at V_{CC} = 4.5 V. The V_{OH} and V_{OL} tests are guaranteed, if not tested, for V_{CC} = 5.5 V. Limits shown apply to operation at V_{CC} = 5.0 V ±0.5 V. Transmission driving tests are performed at V_{CC} = 5.5 V with a 2 ms duration maximum. Transmission driving tests may be performed using V_{IN} = V_{CC} or GND. When V_{IN} = V_{CC} or GND is used, the test is guaranteed for V_{IN} = 2.0 V or 0.8 V.

9/ ΔI_{CC} (max)/pin ≤ 1.6 mA (preferred method), or ΔI_{CC}/package ≤ 1.6 mA x the number of input pins/package where ΔI_{CC} (max)/data pin ≤ 1.6 mA and ΔI_{CC} (max)/control pin ≤ 3.0 mA (alternate method).

10/ The maximum limit for this parameter at 100 krads (Si) is 2 µA.

11/ Power dissipation capacitance (C_{PD}) determines both the power consumption (P_D) and current consumption (I_S). Where:
$P_D = (C_{PD} + C_L) (V_{CC} \times V_{CC})f + (I_{CC} \times V_{CC}) + (n \times d \times \Delta I_{CC} \times V_{CC})$
$I_S = (C_{PD} + C_L) V_{CC}f + I_{CC} + (n \times d \times \Delta I_{CC})$
f is the frequency of the input signal; n is the number of device inputs at TTL levels; d is the duty cycle of the input signal; and C_L is the external output load capacitance.

12/ See EIA/JEDEC STD. No. 78 for electrically induced latch-up test methods and procedures. The values listed for $I_{trigger}$ and V_{over} are to be accurate within ±5 percent.

13/ Tests shall be performed in sequence, attributes data only. Functional tests shall include the truth table and other logic patterns used for fault detection. The test vectors used to verify the truth table shall, at a minimum, test all functions of each input and output. All possible input to output logic patterns per function shall be guaranteed, if not tested, to the truth table in figure 2 herein. Functional tests shall be performed in sequence as approved by the qualifying activity on qualified devices. After incorporating allowable tolerances per MIL-STD-883, V_{IL} = 0.4 V and V_{IH} = 2.4 V. For outputs, L ≤ 0.8 V, H ≥ 2.0 V.

14/ AC limits at V_{CC} = 5.5 V are equal to limits at V_{CC} = 4.5 V and guaranteed by testing at V_{CC} = 4.5 V. Minimum AC limits are guaranteed for V_{CC} = 5.5 V by guardbanding the V_{CC} = 4.5 V minimum limits to 1.5 ns. For propagation delay tests, all paths must be tested.

Device types	01		02, 03	
Case outlines	E	2	C, D, X	2
Terminal number	Terminal symbol			
1	1A	NC	1A	NC
2	1Y	V_{CC}	1B	1A
3	2Y	2B	1Y	1B
4	GND	2A	2A	1Y
5	GND	1B	2B	NC
6	3Y	NC	2Y	2A
7	4Y	1A	GND	NC
8	4B	1Y	4Y	2B
9	4A	2Y	4B	2Y
10	3B	GND	4A	GND
11	3A	NC	3Y	NC
12	V_{CC}	GND	3B	4Y
13	V_{CC}	3Y	3A	4B
14	2B	4Y	V_{CC}	4A
15	2A	4B	- - -	NC
16	1B	NC	- - -	3Y
17	- - -	4A	- - -	NC
18	- - -	3B	- - -	3B
19	- - -	3A	- - -	3A
20	- - -	V_{CC}	- - -	V_{CC}

NC = No connection

Pin description	
Terminal symbol	Description
mA (m = 1 to 4)	Data inputs
mB (m = 1 to 4)	Data inputs
mY (m = 1 to 4)	Data outputs

FIGURE 1. Terminal connections.

Device types 01, 02 and 03

Inputs		Outputs
mA	mB	mY
L	L	L
L	H	L
H	L	L
H	H	H

H = High voltage level
L = Low voltage level

FIGURE 2. Truth table.

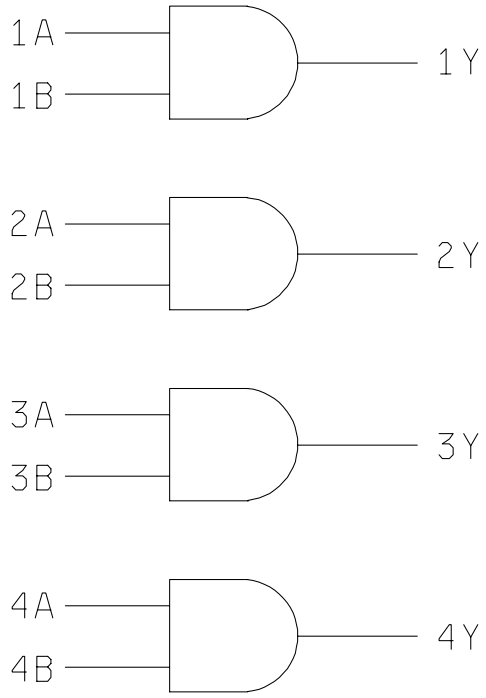
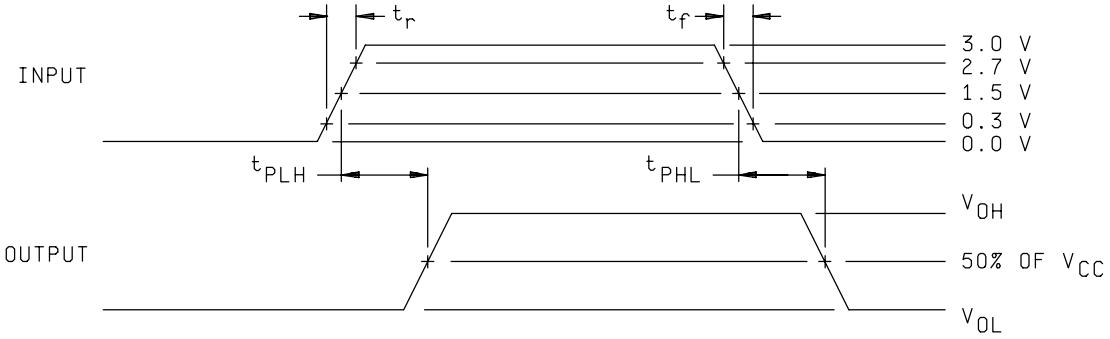
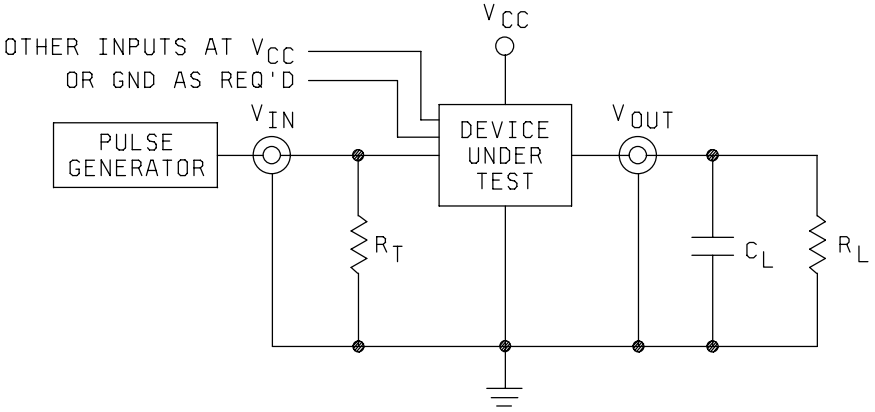


FIGURE 3. Logic diagram.





NOTES:

1. C_L = 50 pF per table I (includes test jig and probe capacitance).
2. R_T = 50Ω, R_L = 500Ω or equivalent.
3. Input signal from pulse generator: V_{IN} = 0.0 V to 3.0 V; PRR ≤ 10 MHz; t_r ≤ 3 ns; t_f ≤ 3 ns; duty cycle = 50 percent.
4. Timing parameters shall be tested at a minimum input frequency of 1 MHz.
5. The outputs are measured one at a time with one transition per measurement.

FIGURE 4. Switching waveforms and test circuit.

4. VERIFICATION

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

4.2.1 Additional criteria for device class M.

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015.

(2) T_A = +125°C, minimum.

b. Interim and final electrical test parameters shall be as specified in table II herein.

4.2.2 Additional criteria for device classes Q and V.

a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.

b. Interim and final electrical test parameters shall be as specified in table II herein.

c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

a. Tests shall be as specified in table II herein.

b. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table in figure 2 herein. The test vectors used to verify the truth table shall, at a minimum, test all functions of each input and output. All possible input to output logic patterns per function shall be guaranteed, if not tested, to the truth table in figure 2, herein. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device.

c. C_{IN} and C_{PD} shall be measured only for initial qualification and after process or design changes which may affect capacitance. C_{IN} shall be measured between the designated terminal and GND at a frequency of 1 MHz. C_{PD} shall be tested in accordance with the latest revision of JEDEC Standard No. 20 and table I herein. For C_{IN} and C_{PD}, test all applicable pins on five devices with zero failures.

d. Latch-up tests are required for device class V. These tests shall be performed only for initial qualification and after process or design changes which may affect the performance of the device. Latch-up tests shall be considered destructive. For latch-up tests, test all applicable pins on five devices with zero failures.

TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	- - -	- - -	1
Final electrical parameters (see 4.2)	1/ 1, 2, 3, 7, 8, 9	1/ 1, 2, 3, 7, 8, 9, 10, 11	2/ 3/ 1, 2, 3, 7, 8, 9, 10, 11
Group A test requirements (see 4.4)	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11
Group C end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	3/ 1, 2, 3, 7,8, 9, 10, 11
Group D end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3
Group E end-point electrical parameters (see 4.4)	1, 7, 9	1, 7, 9	1, 7, 9

1/ PDA applies to subgroup 1.
2/ PDA applies to subgroups 1, 7, and deltas.
3/ Delta limits, as specified in table III, shall be required where specified and the delta limits shall be completed with reference to the zero hour electrical parameters.

TABLE III. Burn-in and operating life test, delta parameters (+25°C).

Parameter 1/	Symbol	Device type	Delta limits
Supply current	I_{CCH}, I_{CCL}	02	±100 nA 2/
		03	±150 nA
Supply current delta	ΔI_{CC}	03	±0.4 mA
Input current low level	I_{IL}	03	±20 nA
Input current high level	I_{IH}	03	±20 nA
Output voltage low level V_{CC} = 5.5 V, I_{OL} = 24 mA	V_{OL}	03	±0.04 V
Output voltage high level V_{CC} = 5.5 V, I_{OH} = -24 mA	V_{OH}	03	±0.20 V

1/ These parameters shall be recorded before and after required burn-in and life test to determine delta limits.
2/ Guaranteed, if not tested.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

b. T_A = +125°C, minimum.

c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

a. End-point electrical parameters shall be as specified in table II herein.

b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table II herein.

c. RHA tests for device classes M, Q, and V for levels M, D, P, L, R, and F shall be performed through each level to determine at what levels the devices meet the RHA requirements. These RHA tests shall be performed for initial qualification and after design or process changes which may affect the RHA performance of the device.

b. Prior to irradiation, each selected sample shall be assembled in its qualified package. It shall pass the specified group A electrical parameters in table I for subgroups specified in table II herein.

4.4.4.1 Total dose irradiation testing. Total dose irradiation testing shall be performed in accordance with MIL-STD-883, method 1019, condition A and as specified herein. Prior to and during total dose irradiation characterization and testing, the devices for characterization shall be biased so that 50 percent are at inputs high and 50 percent are at inputs low, and the devices for testing shall be biased to the worst case condition established during characterization. Devices shall be biased as follows:

a. Device type 02:

(1) Inputs tested high, V_{CC} = 5.5 V dc +5%, R_{CC} = 10 Ω +20%, V_{IN} = 5.0 V dc +5%, R_{IN} = 1 kΩ +20%, and all outputs are open.

(2) Inputs tested low, V_{CC} = 5.5 V dc +5%, R_{CC} = 10 Ω +20%, V_{IN} = 0.0 V dc, R_{IN} = 1 kΩ +20%, and all outputs are open.

b. Device type 03:

(1) Inputs tested high, V_{CC} = 5.5 V dc ±5%, V_{IN} = 5.0 V dc +10%, R_{IN} = 1 kΩ ±20%, and all outputs are open.

(2) Inputs tested low, V_{CC} = 5.5 V dc ±5%, V_{IN} = 0.0 V dc, R_{IN} = 1 kΩ ±20%, and all outputs are open.

4.4.4.1.1 Accelerated aging test. Accelerated aging shall be performed on classes M, Q, and V devices requiring an RHA level greater than 5K rads (Si). The post-anneal end-point electrical parameter limits shall be as specified in table I herein and shall be the preirradiation end-point electrical parameter limit at 25°C ± 5°C. Testing shall be performed at initial qualification and after any design or process changes which may affect the RHA response of the device.

4.5 Methods of inspection. Methods of inspection shall be specified as follows:

4.5.1 Voltage and current. Unless otherwise specified, all voltages given are referenced to the microcircuit GND terminal. Currents given are conventional current and positive when flowing into the referenced terminal.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform Defense Supply Center Columbus (DSCC) when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.

6.4 Comments. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0547.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 04-08-18

Approved sources of supply for SMD 5962-89547 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard microcircuit drawing PIN 1/	Vendor CAGE number	Vendor similar PIN 2/
5962-8954701EA	3/	54ACT11008
5962-89547012A	3/	54ACT11008
5962-8954702CA	01295 27014	SNJ54ACT08J 54ACTQ08DMQB
5962-8954702DA	01295 27014	SNJ54ACT08W 54ACTQ08FMQB
5962-89547022A	01295 27014	SNJ54ACT08FK 54ACTQ08LMQB
5962-8954702VCA	3/	54ACTQ08J-QMLV
5962-8954702VDA	3/	54ACTQ08W-QMLV
5962-8954702V2A	3/	54ACTQ08E-QMLV
5962R8954702CA	27014	54ACTQ08DMQB-RH
5962R8954702DA	27014	54ACTQ08FMQB-RH
5962R89547022A	27014	54ACTQ08LMQB-RH
5962R8954702VCA	27014	54ACTQ08JRQMLV
5962R8954702VDA	27014	54ACTQ08WRQMLV
5962R8954702V2A	27014	54ACTQ08ERQMLV
5962-8954703XA	F8859	54ACT08K02Q
5962-8954703XC	F8859	54ACT08K01Q
5962-8954703VXA	F8859	54ACT08K02V
5962-8954703VXC	F8859	54ACT08K01V
5962F8954703XA	F8859	RHFACT08K02Q
5962F8954703XC	F8859	RHFACT08K01Q
5962F8954703VXA	F8859	RHFACT08K02V
5962F8954703VXC	F8859	RHFACT08K01V

See footnotes on next page.

1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the Vendor to determine its availability.
2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
3/ No longer available from an approved source of supply.

Vendor CAGE number	Vendor name and address
27014	National Semiconductor 2900 Semiconductor Drive P. O. Box 58090 Santa Clara, CA 95052-8090
01295	Texas Instruments Incorporated Semiconductor Group 8505 Forest Ln. P. O. Box 660199 Dallas, TX 75243 Point of contact: U.S. Highway 75 South P. O. Box 84, M/S 853 Sherman, TX 75090-9493
F8859	STMicroelectronics 3 rue de Suisse BP4199 35041 RENNES cedex2-FRANCE